

IN THE CLAIMS: .

This listing of claims will replace all prior versions, and listings, of claims in this application:

1-41 (Canceled).

42. (Currently Amended) A camera having at least ~~one~~ a reflection type liquid crystal device, said reflection type liquid crystal device comprising:

a thin film transistor being formed over a first substrate;

an interlayer insulating film being formed over the thin film transistor and the first substrate;

a pixel electrode comprising a metal and being formed over the interlayer insulating film; and

a reflection layer comprising a dielectric multi-layer film and being formed on the pixel electrode;

wherein convex or concave portions are formed on the interlayer insulating film, so that a surface of the pixel electrode has convex or concave portions;

wherein the dielectric multi-layer film comprises a first thin film having a first refractive index and a second thin film having a second refractive index formed on the first thin film;

wherein the second refractive index is higher than the first refractive index;

wherein the second refractive index is in a range of 1.8 to 6.0; and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

43. (Previously Presented) A camera device according to claim 42,

wherein a film thickness d_1 of said first thin film is so adjusted as to satisfy $400 \text{ nm} \leq \lambda_1 \leq 500 \text{ nm}$ ($\lambda_1 = 4n_1d_1$), where the film thickness and the refractive index of said first thin film are d_1 and n_1 , respectively; and

wherein a film thickness d_2 of said second thin film is so adjusted as to satisfy $450 \text{ nm} \leq \lambda_2 \leq 700 \text{ nm}$ ($\lambda_2 = 4n_2d_2$), where the film thickness and the refractive index of said second thin film are d_2 and n_2 , respectively.

44-46. (Cancelled)

47. (Previously Presented) A camera according to claim 42, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

48. (Previously Presented) A camera according to claim 42, wherein the pixel electrode is formed on the interlayer insulating film in contact therewith.

49. (Previously Presented) A camera according to claim 42, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrates; a thin film transistor being connected to the pixel electrode; and the reflection layer.

50. (Previously Presented) A camera according to claim 42, wherein the camera is a digital

camera.

51. (Previously Presented) A camera according to claim 42, wherein the camera is a digital still camera.

52. (Currently Amended) A personal computer having at least ~~one~~ a reflection type liquid crystal device, said reflection type liquid crystal device comprising:

a thin film transistor being formed over a first substrate; an interlayer insulating film being formed over the thin film transistor and the first substrate;

a pixel electrode comprising a metal and being formed over the interlayer insulating film;

a reflection layer comprising a dielectric multi-layer film and being formed on the pixel electrode;

wherein convex or concave portions are formed on the interlayer insulating film, so that a surface of the pixel electrode has convex or concave portions;

wherein the dielectric multi-layer film comprises a first thin film having a first refractive index and a second thin film having a second refractive index formed on the first thin film;

wherein the second refractive index is higher than the first refractive index; and

wherein the second refractive index is in a range of 1.8 to 6.0, and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

53. (Previously Presented) A personal computer according to claim 52,

wherein a film thickness d_1 of said first thin film is so adjusted as to satisfy $400 \text{ nm} \leq \lambda_1 \leq 500 \text{ nm}$ ($\lambda_1 = 4n_1d_1$), where the film thickness and the refractive index of said first thin film are d_1 and n_1 , respectively, and a film thickness d_2 of said second thin film is so adjusted as to satisfy $450 \text{ nm} \leq \lambda_2 \leq 700 \text{ nm}$ ($\lambda_2 = 4n_2d_2$), where the film thickness and the refractive index of said second thin film are d_2 and n_2 , respectively.

54-56. (Cancelled)

57. (Previously Presented) A personal computer according to claim 52, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

58. (Previously Presented) A personal computer according to claim 52, wherein the pixel electrode is formed on the interlayer insulating film in contact therewith.

59. (Previously Presented) A personal computer according to claim 52, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrates; a thin film transistor being connected to the pixel electrode; and the reflection layer.

60. (Currently Amended) A cellular phone having at least ~~one~~ a reflection type liquid crystal device, said reflection type liquid crystal device comprising:

a thin film transistor being formed over a first substrate;
an interlayer insulating film being formed over the thin film transistor and the first substrate;
a pixel electrode comprising a metal and being formed over the interlayer insulating film; and
a reflection layer comprising a dielectric multi-layer film and being formed on the pixel electrode;

wherein convex or concave portions are formed on the interlayer insulating film, so that a surface of the pixel electrode has convex or concave portions;

wherein the dielectric multi-layer film comprises a first thin film having a first refractive index and a second thin film having a second refractive index formed on the first thin film;

wherein the second refractive index is higher than the first refractive index;

wherein the second refractive index is in a range of 1.8 to 6.0; and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

61. (Previously Presented) A cellular phone device according to claim 60,

wherein a film thickness d_1 of said first thin film is so adjusted as to satisfy $400 \text{ nm} \leq \lambda_1 \leq 500 \text{ nm}$ ($\lambda_1 = 4n_1d_1$), where the film thickness and the refractive index of said first thin film are d_1 and n_1 , respectively; and

wherein a film thickness d_2 of said second thin film is so adjusted as to satisfy $450 \text{ nm} \leq \lambda_2 \leq 700 \text{ nm}$ ($\lambda_2 = 4n_2d_2$), where the film thickness and the refractive index of said second thin film are d_2 and n_2 , respectively.

62. (Previously Presented) A cellular phone according to claim 60, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

63. (Previously Presented) A cellular phone according to claim 60, wherein the pixel electrode is formed on an interlayer insulating film in contact therewith.

64. (Previously Presented) A cellular phone according to claim 60, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrate; the thin film transistor being connected to the pixel electrode; and the reflection layer.

65-67. (Cancelled)

68. (Currently Amended) An electronic device having an active matrix display device comprising:

a switching element formed over a first substrate;

a first interlayer insulating film formed over the switching element;

a second interlayer insulating film comprising an organic resin formed over the first interlayer insulating film, a surface of said second interlayer insulating film having a plurality of first protrusions;

a pixel electrode formed over the plurality of first protrusions, a surface of said pixel

electrode having a plurality of second protrusions;

a first dielectric layer formed over the pixel electrode, said first dielectric layer having a first refractive index;

a second dielectric layer formed on the first dielectric layer, said second dielectric layer having a second refractive index ~~wherein said second dielectric layer has a different refractive index from said first dielectric layer~~; and

an orientation film formed on the second dielectric layer;

wherein the second refractive index is higher than the first refractive index;

wherein the second refractive index is in a range of 1.8 to 6.0; and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

69. (Previously Presented) An electronic device according to claim 68, wherein the first dielectric layer comprises a material selected from the group consisting of SiO_2 , MgF_2 , Na_3AlF_6 .

70. (Previously Presented) An electronic device according to claim 68, wherein the second dielectric layer comprises a material from the group consisting of TiO_2 , ZrO_2 , Ta_2O_5 , ZnS , ZnSe , ZnTe , Si , Ge , Y_2O_3 and Al_2O_3 .

71. (Currently Amended) ~~A camera~~ An electronic device having an active matrix display device comprising:

a switching element formed over a first substrate;

a first interlayer insulating film formed over the switching element;

a second interlayer insulating film comprising an organic resin formed over the first interlayer insulating film, ~~a surface of~~ said second interlayer insulating film having ~~a plurality of first protrusions~~ a leveled surface;

a pixel electrode formed over the ~~plurality of first protrusions~~ leveled surface, a surface of said pixel electrode having a plurality of ~~second~~ protrusions;

a first dielectric layer formed over the ~~pixel electrode~~ plurality of protrusions;

a second dielectric layer formed on the first dielectric layer, wherein said second dielectric layer has a different refractive index from said first dielectric layer; and

an orientation film formed on the second dielectric layer.

72. (Currently Amended) ~~A camera~~ An electronic device according to claim 71, wherein the first dielectric layer comprises a material selected from the group consisting of SiO_2 , MgF_2 , Na_3AlF_6 .

73. (Currently Amended) ~~A camera~~ An electronic device according to claim 71, wherein the second dielectric layer comprises a material from the group consisting of TiO_2 , ZrO_2 , Ta_2O_5 , ZnS , ZnSe , ZnTe , Si , Ge , Y_2O_3 and Al_2O_3 .

74. (Currently Amended) ~~A camera~~ An electronic device according to claim 71, wherein the ~~camera~~ electronic device is a digital camera.

75. (Currently Amended) ~~A camera~~ An electronic device according to claim 71, wherein the ~~camera~~ electronic device is a digital still camera.

76. (Currently Amended) ~~A cellular phone~~ An electronic device having an active matrix display device comprising:

a switching element formed over a first substrate;

a first interlayer insulating film formed over the switching element;

a second interlayer insulating film comprising an organic resin formed over the first interlayer insulating film, ~~a surface of~~ said second interlayer insulating film having ~~a plurality of first protrusions~~ a first leveled surface;

a pixel electrode formed over the ~~plurality of first protrusions~~ first leveled surface, a surface of said pixel electrode having a plurality of ~~second protrusions~~ comprising an oxidation film;

a first dielectric layer having a second leveled surface formed over the ~~pixel electrode~~ plurality of protrusions;

a second dielectric layer formed on the second leveled surface of the first dielectric layer, wherein said second dielectric layer has a different refractive index from said first dielectric layer; and

an orientation film formed on the second dielectric layer.

77. (Currently Amended) ~~A cellular phone~~ An electronic device according to claim 76, wherein the first dielectric layer comprises a material selected from the group consisting of SiO₂, MgF₂, Na₃AlF₆.

78. (Currently Amended) ~~A cellular phone~~ An electronic device according to claim 76, wherein the second dielectric layer comprises a material from the group consisting of TiO_2 , ZrO_2 , Ta_2O_5 , ZnS , ZnSe , ZnTe , Si , Ge , Y_2O_3 and Al_2O_3 .

79. (New) An electronic device according to claim 71, wherein the second refractive index is higher than the first refractive index; wherein the second refractive index is in a range of 1.8 to 6.0; and wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

80. (New) An electronic device according to claim 76, wherein the second refractive index is higher than the first refractive index; wherein the second refractive index is in a range of 1.8 to 6.0; and wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.